MMBTA14LT1 is a Preferred Device

Darlington Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CES}	30	Vdc
Collector - Base Voltage	V _{CBO}	30	Vdc
Emitter – Base Voltage	V _{EBO}	10	Vdc
Collector Current – Continuous	I _C	300	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25 C	P _D	225 1.8	mv/ nW/°C
Thermal Resistance, June ich-te-/ mbient	E. J.	556	CW
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

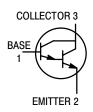
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



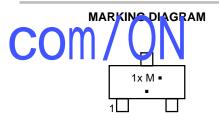
ON Semiconductor®

http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6



1x = Device Code

x = M for MMBTA13LT1

x = N for MMBTA14LT1

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA13LT1	SOT-23	3,000 / Tape & Reel
MMBTA13LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA14LT1	SOT-23	3,000 / Tape & Reel
MMBTA14LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, V_{BE} = 0$)		V _{(BR)CES}	30	-	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)		I _{CBO}	_	100	nAdc
Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)		I _{EBO}	_	100	nAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	MMBTA13 MMBTA14	h _{FE}	5000 10,000	- -	-
$(I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBTA13 MMBTA14		10,000 20,000	<u>-</u> -	
Collector – Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 0.1 mAdc)		V _{CE(sat)}	_	1.5	Vdc
Base – Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)		V_{BE}	_	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note 4) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	125	_	MHz

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

^{4.} $f_T = |h_{fe}| \bullet f_{test}$.

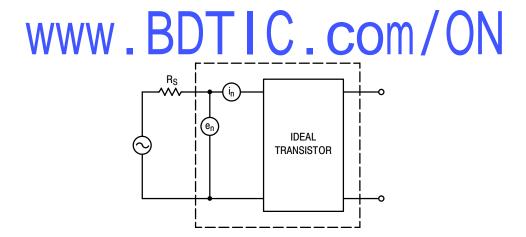


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

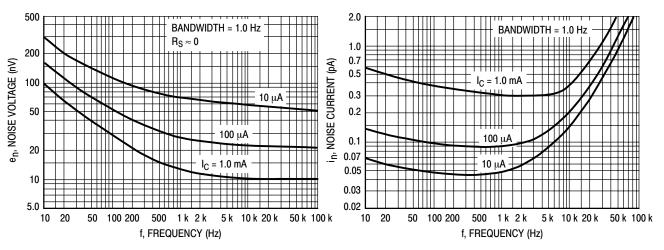


Figure 2. Noise Voltage

Figure 3. Noise Current

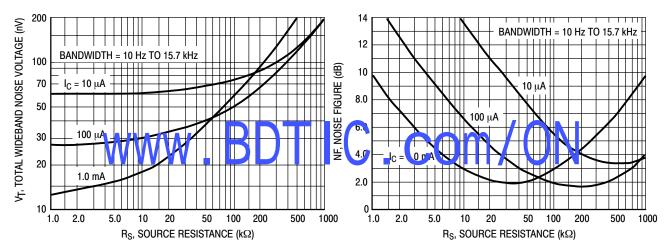


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

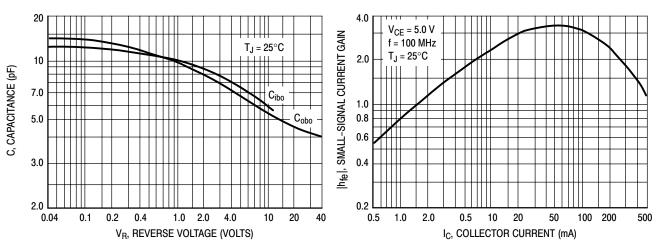


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

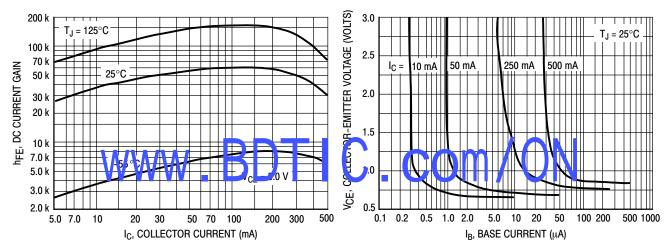


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

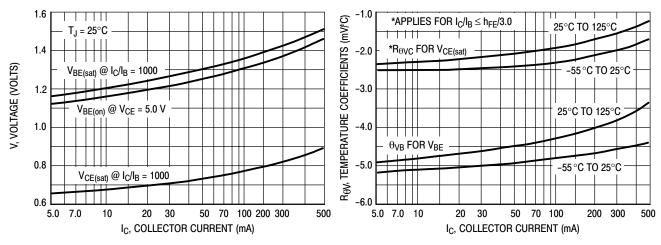


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

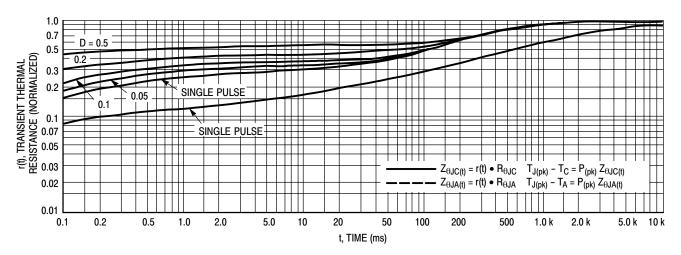


Figure 12. Thermal Response

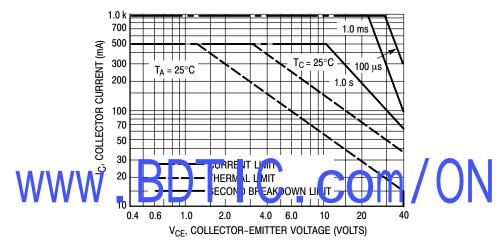
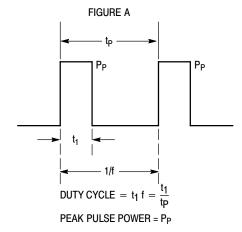


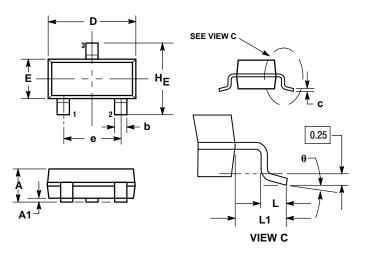
Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



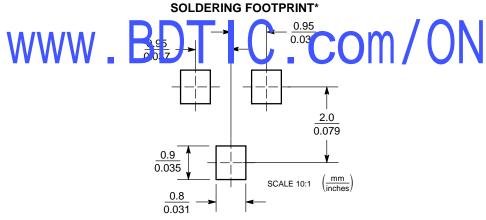
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE 2. EMITTER
 - COLLECTOR



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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